

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for fabricating a SiGe film, comprising the steps of:

preparing a Si substrate,

forming a SiGe film over said Si substrate, substrate without an enveloping layer, and

forming 90 degrees dislocations at a bottom region of said SiGe film adjacent to an interface of said SiGe film and said Si substrate.

2. (Original) The fabricating method as defined in claim 1, further comprising the step of forming an interfacial layer between said Si substrate and said SiGe film.

3. (Original) The fabricating method as defined in claim 2, wherein said interfacial layer contains Ge.

4. (Original) The fabricating method as defined in claim 3, further comprising the step of forming a SiGe intermediate layer between said interfacial layer and said SiGe film.

5. (Original) The fabricating method as defined in claim 3, wherein a thickness of said interfacial layer is set within 0.1-10nm.

6. (Original) The fabricating method as defined in claim 2, wherein said interfacial layer contains GaAs.

7. (Original) The fabricating method as defined in claim 6, wherein a thickness of said interfacial layer is set within 0.1-10nm.

8. (Currently Amended) A substrate for epitaxial growth, comprising:  
a Si substrate,

a SiGe film without an enveloping layer formed over said Si substrate and containing 90 degrees dislocations at a bottom region thereof adjacent to an interface of said SiGe film and said Si substrate.

9. (Original) The substrate as defined in claim 8, further comprising an interfacial layer between said Si substrate and said SiGe film.

10. (Original) The substrate as defined in claim 9, wherein said interfacial layer contains Ge.

11. (Original) The substrate as defined in claim 10, further comprising a SiGe intermediate layer between said interfacial layer and said SiGe film.

12. (Original) The substrate as defined in claim 10, wherein a thickness of said interfacial layer is set within 0.1-10nm.

13. (Original) The substrate as defined in claim 9, wherein said interfacial layer contains GaAs.

14. (Original) The substrate as defined in claim 13, wherein a thickness of said interfacial layer is set within 0.1-10nm.

15. (Original) A multilayered structure comprising:

a substrate for epitaxial growth as defined in claim 8, and

a Si film formed on said substrate.